

REVISIONS

LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
	查询"5962-9681501QXA"供应商		

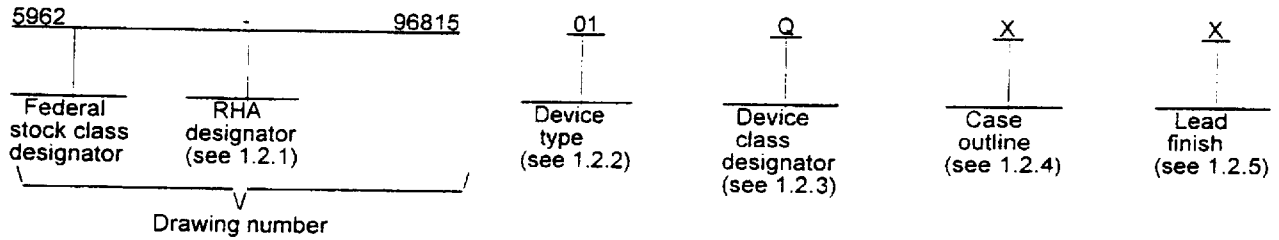
REV																				
SHEET																				
REV																				
SHEET	15	16																		
REV STATUS OF SHEETS		REV																		
		SHEET		1	2	3	4	5	6	7	8	9	10	11	12	13	14			
PMIC N/A		PREPARED BY Joseph A. Kerby				DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216														
STANDARD MICROCIRCUIT DRAWING THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE AMSC N/A		CHECKED BY Charles F. Saffle, Jr.				MICROCIRCUIT, DIGITAL, ADVANCED BIPOLAR CMOS, 8-BIT TTL/BTL TRANSCEIVER WITH THREE-STATE OUTPUTS, MONOLITHIC SILICON														
		APPROVED BY Monica L. Poelking																		
		DRAWING APPROVAL DATE 96-06-12				SIZE A	CAGE CODE 67268	5962-96815												
		REVISION LEVEL				SHEET 1 OF 16														

DISTRIBUTION STATEMENT A Approved for public release, distribution is unlimited.

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Circuit function</u>
01	54FB2040	8-bit TTL/BTL transceivers with three-state outputs

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

<u>Device class</u>	<u>Device requirements documentation</u>
M	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

<u>Outline letter</u>	<u>Descriptive designator</u>	<u>Terminals</u>	<u>Package style</u>
X	GDFP1-F56	56	Ceramic flat pack

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 2

1.3 Absolute maximum ratings. 1/ 2/ 3/

Supply voltage range (V_{CC})	-0.5 V dc to +7.0 V dc
Input voltage range applied to any Bn outputs in the disabled or power-off state (V_{OUT})	-0.5 V dc to +3.5 V dc
Voltage range applied to any output in the high state (A port)	-0.5 V to V_{CC}
DC input voltage range (V_{IN}):	
except Bn ports	-1.2 V dc to +7.0 V dc 4/
Bn ports	-1.2 V dc to 3.5 V 4/
DC input clamp current (I_{IK}):	
except Bn ports	-40 mA
Bn ports	-18 mA
DC output current (I_{OL}) per output:	
A port	+48 mA
Bn ports	+200 mA
Operating case temperature range, (T_C)	-55°C to 125°C
Maximum power dissipation (P_D)	1345 mW 5/
Storage temperature range (T_{STG})	-65°C to +150°C
Lead temperature (soldering, 10 seconds)	+300°C
Thermal resistance, junction-to-case (Θ_{JC})	See MIL-STD-1835
Junction temperature (T_J)	+175°C

1.4 Recommended operating conditions. 2/ 3/

Supply voltage range (V_{CC} , BIAS V_{CC} , BG V_{CC})	+4.75 V dc to +5.25 V dc
High level input voltage range (V_{IH}):	
Bn ports	+1.62 V to 2.3 V 6/
Except Bn ports	+2.0 V
Low level input voltage range (V_{IL}):	
Bn ports	+0.75 V to 1.47 V 6/
Except Bn ports	+0.8 V
DC input clamp current (I_{IK})	-18 mA
Maximum low level output current (I_{OL}) Bn ports	+100 mA
Operating case temperature range (T_C)	-55°C to +125°C

1.5 Digital logic testing for device classes Q and V.

Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012)	XX percent 7/
---	---------------

- 1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- 2/ Unless otherwise noted, all voltages are referenced to GND.
- 3/ The limits for the parameters specified herein shall apply over the full specified V_{CC} range and case temperature range of -55°C to +125°C. Unused inputs must be held high or low.
- 4/ The input negative voltage rating may be exceeded provided that the input clamp current rating is observed.
- 5/ Power dissipation values are derived using the formula $P_D = V_{CC}I_{CC} + nV_{OL}I_{OL}$, where V_{CC} and I_{OL} are as specified in 1.4 above, I_{CC} and V_{OL} are as specified in table I herein, and n represents the total number of outputs.
- 6/ This parameter is based on characterization data, but is not tested.
- 7/ Values will be added when they become available.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 3

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

MILITARY

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.
MIL-STD-973 - Configuration Management.
MIL-STD-1835 - Microcircuit Case Outlines.

HANDBOOK

MILITARY

MIL-HDBK-103 - List of Standard Microcircuit Drawings (SMD's).
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Non-Government publications. The following document(s) form a part of this document to the extent specified herein. Unless otherwise specified, the issues of the documents which are DOD adopted are those listed in the issue of the DODISS cited in the solicitation. Unless otherwise specified, the issues of documents not listed in the DODISS are the issues of the documents cited in the solicitation.

INSTITUTE OF ELECTRICAL AND ELECTRONICS ENGINEERS (IEEE)

IEEE Standard 1149.1 - IEEE Standard Test Access Port and Boundary Scan Architecture.

IEEE Standard 1194.1 - IEEE Standard for Electrical Characteristics of Backplane Transceiver Logic (BTL) Interface Circuits.

(Applications for copies should be addressed to the Institute of Electrical and Electronics Engineers, 445 Hoes Lane, Piscataway, NJ 08854-4150.)

(Non-Government standards and other publications are normally available from the organizations that prepare or distribute the documents. These documents may also be available in or through libraries or other informational services.)

2.3 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Truth table. The truth table shall be as specified on figure 2.

3.2.4 Logic diagram. The logic diagram shall be as specified on figure 3.

3.2.5 Switching waveforms and test circuit. The switching waveforms and test circuit shall be as specified on figure 4.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 4

DESC FORM 193A
JUL 94

9004708 0027756 069

3.2.7 Radiation exposure circuit. The radiation exposure circuit shall be as specified when available.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change for device class M. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.

3.9 Verification and review for device class M. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 126 (see MIL-PRF-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.

(2) $T_A = +125^\circ\text{C}$, minimum.

b. Interim and final electrical test parameters shall be as specified in table II herein.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 5

TABLE I. Electrical performance characteristics.

Test and test method 1/	Symbol	Test conditions 2/ -55°C ≤ T _C ≤ +125°C +4.5 V ≤ V _{CC} ≤ +5.5 V unless otherwise specified	V _{CC}	Group A subgroups	Limits 3/		Unit	
					Min	Max		
Negative input clamp voltage 3022	V _{IK}	Bn port, I _{IN} = -18 mA	4.5 V	1, 2, 3		-1.2	V	
		Except Bn port, I _{IN} = -40 mA				-1.2		
High level output voltage, AOn port 3006	V _{OH}	I _{OH} = -3.0 mA	4.5 V	1, 2, 3	2.5		V	
Low level output voltage 3007	V _{OL}	AOn port	4.5 V	1, 2, 3		0.5	V	
		Bn port			I _{OL} = 24 mA	0.75		1.1
					I _{OL} = 80 mA			1.2
		I _{OL} = 100 mA						
Input current, Except Bn port	I _{IN}	For input under test, V _{IN} = 5.5 V	5.5 V	1, 2, 3		50	μA	
Input current high, Except Bn port 3010	I _{IH} 4/	For input under test, V _{IN} = 2.7 V	5.5 V	1, 2, 3		50	μA	
Input current low 3009	I _{IL} 4/	Except Bn port, V _{IN} = 0.5 V	5.5 V	1, 2, 3		-50	μA	
		Bn port, V _{IN} = 0.75 V				-100		
Output current	I _{OH}	Bn port, V _{OUT} = 2.1 V	0.0 V and 5.5 V	1, 2, 3		100	μA	
Three-state output leakage current high 3021	I _{OZH} 5/	AOn port, V _{OUT} = 2.7 V	5.5 V	1, 2, 3		50	μA	
Three-state output leakage current low 3020	I _{OZL} 5/	AOn port, V _{OUT} = 0.5 V	5.5 V	1, 2, 3		-50	μA	
Output short-circuit current	I _{OS} 6/	AOn port, V _{OUT} = 0.0 V	5.5 V	1, 2, 3	-30	-170	mA	
Quiescent supply current 3005	I _{CC}	For all inputs, V _{IN} = V _{CC} or GND I _{OUT} = 0 A	5.5 V	1, 2, 3		40	mA	
						70		
Input capacitance 3012	C _{IN}	T _C = +25°C, V _{IN} = V _{CC} or GND See 4.4.1b	5.0 V	4		9.9	pF	
						9.9		
Output capacitance, AOn port 3012	C _{OUT}	T _C = +25°C, V _{OUT} = V _{CC} or GND See 4.4.1b	5.0 V	4		14.7	pF	

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 6

DESC FORM 193A
JUL 94

9004708 0027758 931

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ -55°C ≤ T _C ≤ +125°C +4.5 V ≤ V _{CC} ≤ +5.5 V unless otherwise specified	V _{CC}	Group A subgroups	Limits 3/		Unit
					Min	Max	
I/O port capacitance	C _{I/O} 7/	Bn port per P1194.0 See 4.4.1b	0.0 V and 4.5 V	4		8	pF
			4.5 V and 5.5 V			9	
Functional test	8/	V _{IN} = V _{IH} Min or V _{IL} Max Verify output V _O See 4.4.1d	4.5 V	7, 8	L	H	
			5.5 V		7, 8	L	

Live-insertion specification

Quiescent supply current 3005	I _{CC} (BIAS V _{CC})	V _B = 0 to 2.0 V V _I (BIAS V _{CC}) = 4.5 V or 5.5 V	0.0 V and 4.5 V	1, 2, 3		450	μA	
			4.5 V and 5.5 V		1, 2, 3			10
Output voltage, Bn port	V _{OUT}	V _I (BIAS V _{CC}) = 5.0 V T _A = 25°C	0.0 V	1, 2, 3	1.62	2.1	V	
Output current, Bn port	I _{OUT} 5/	V _B = 1.0 V, V _I (BIAS V _{CC}) = 4.5 V to 5.5 V OEB = 0.0 V to 0.8 V	0.0 V	1, 2, 3	-30		μA	
			0.0 V and 5.5 V					100
			0.0 V and 2.2 V					100

Switching characteristics

Propagation delay time, AIn to Bn 3003	t _{PLH1} 9/	C _L = 50 pF minimum, R _L = 500Ω, See figure 4	5.0 V	9	2.5	6.0	ns
			4.5 V and 5.5 V		10, 11	0.5	
	t _{PHL1} 9/		5.0 V	9	1.8	5.8	ns
			4.5 V and 5.5 V		10, 11	0.5	
Propagation delay time, Bn to AOn 3003	t _{PLH2} 9/	C _L = 50 pF minimum, R _L = 500Ω, See figure 4	5.0 V	9	1.5	5.7	ns
			4.5 V and 5.5 V		10, 11	0.4	
	t _{PHL2} 9/		5.0 V	9	2.3	5.9	ns
			4.5 V and 5.5 V		10, 11	0.8	

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 7

TABLE I. Electrical performance characteristics - Continued.

Test and test method 1/	Symbol	Test conditions 2/ -55°C ≤ T _C ≤ +125°C +4.5 V ≤ V _{CC} ≤ +5.5 V unless otherwise specified	V _{CC}	Group A subgroup s	Limits 3/		Unit
					Min	Max	
Propagation delay time, OEB to Bn 3003	t _{PLH3} g/	C _L = 30 pF minimum R _L = 16.5Ω See figure 4	5.0 V	9	3.3	6.7	ns
			4.5 V and 5.5 V	10, 11	0.5	9.9	
	t _{PHL3} g/		5.0 V	9	3.1	6.2	
			4.5 V and 5.5 V	10, 11	0.4	9.5	
Propagation delay time, OEB to Bn 3003	t _{PLH4} g/	C _L = 30 pF minimum R _L = 16.5Ω See figure 4	5.0 V	9	3.2	6.8	ns
			4.5 V and 5.5 V	10, 11	1.3	9.5	
	t _{PHL4} g/		5.0 V	9	2.9	6.0	
			4.5 V and 5.5 V	10, 11	0.2	9.8	
Propagation delay time, output enable, OEA to AOn 3003	t _{PZH} g/	C _L = 50 pF minimum, R _L = 500Ω, See figure 4	5.0 V	9	1.7	5.5	ns
			4.5 V and 5.5 V	10, 11	1.2	8.0	
	t _{PZL} g/		5.0 V	9	1.5	5.1	
			4.5 V and 5.5 V	10, 11	0.8	7.5	
Propagation delay time, output disable, OEA to AOn 3003	t _{PHZ} g/	C _L = 50 pF minimum, R _L = 500Ω, See figure 4	5.0 V	9	1.8	5.9	ns
			4.5 V and 5.5 V	10, 11	1.0	8.2	
	t _{PLZ} g/		5.0 V	9	1.0	4.7	
			4.5 V and 5.5 V	10, 11	0.4	7.2	
Rise time, 1.3 V to 1.8 V, Bn port	t _r	C _L = 30 pF minimum, R _L = 16.5Ω, See figure 4	5.0 V	9	0.2	3.8	ns
			4.5 V and 5.5 V	10, 11	0.2	4.5	
Fall time, 1.8 V to 1.3 V, Bn port	t _f	C _L = 30 pF minimum, R _L = 16.5Ω, See figure 4	5.0 V	9	1.0	3.0	ns
			4.5 V and 5.5 V	10, 11	0.9	4.0	

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 8

DESC FORM 193A
JUL 94

9004708 0027760 59T

TABLE I. Electrical performance characteristics - Continued.

- 1/ For tests not listed in the referenced MIL-STD-883, utilize the general test procedure of 883 under the conditions listed herein.
- 2/ Each input/output, as applicable, shall be tested at the specified temperature, for the specified limits, to the tests in table I herein. Output terminals not designated shall be high level logic, low level logic, or open, except for all I_{CC} tests, where the output terminals shall be open. When performing these tests, the current meter shall be placed in the circuit such that all current flows through the meter. For input terminals not designated, $V_{IN} = \text{GND}$ or $V_{IN} \geq 3.0 \text{ V}$.
- 3/ For negative and positive voltage and current values, the sign designates the potential difference in reference to GND and the direction of current flow, respectively, and the absolute value of the magnitude, not the sign, is relative to the minimum and maximum limits, as applicable, listed herein.
- 4/ For I/O ports, the parameters I_{IH} and I_{IL} include the off-state output current.
- 5/ The parameters I_{OZH} and I_{OZL} include the input leakage current. This test shall be guaranteed, if not tested, to the limits specified in table I herein, when performed with control inputs that affect the state of the output under test at $V_{IN} = 0.8 \text{ V}$ or 2.0 V .
- 6/ Not more than one output should be tested at one time, and the duration of the test condition should not exceed one second.
- 7/ This parameter does not meet the (BTL) specification IEEE 1194.0.
- 8/ Tests shall be performed in sequence, attributes data only. Functional tests shall include the truth table and other logic patterns used for fault detection. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2 herein. Functional tests shall be performed in sequence as approved by the qualifying activity on qualified devices. Allowable tolerances per MIL-STD-883 may be incorporated. For A outputs, $L \leq 0.8 \text{ V}$, $H \geq 2.0 \text{ V}$. For B outputs, $L \leq 1.2 \text{ V}$, H is dependent on the pull-up circuit.
- 9/ For propagation delay tests, all paths must be tested.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 9

DESC FORM 193A
JUL 94

■ 9004708 0027761 426 ■

查询"5962-9681501QXA"集成电路

Device type		01	
Case outline		X	
Terminal number	Terminal symbol	Terminal number	Terminal symbol
1	NC	29	NC
2	OEB	30	AO8
3	OEA	31	TDO
4	BIAS V _{CC}	32	TDI
5	V _{CC}	33	V _{CC}
6	AO1	34	A18
7	A11	35	GND
8	AO2	36	B8
9	GND	37	GND
10	A12	38	B7
11	A13	39	GND
12	AO3	40	B6
13	GND	41	GND
14	AO4	42	B5
15	GND	43	GND
16	A14	44	B4
17	A15	45	GND
18	AO5	46	B3
19	GND	47	GND
20	AO6	48	B2
21	GND	49	GND
22	A16	50	B1
23	GND	51	GND
24	AO7	52	TMS
25	BG V _{CC}	53	V _{CC}
26	A17	54	TCK
27	BG GND	55	OEB
28	NC	56	NC

Note: Pins are allocated for the four-wire IEEE 1149.1 (JTAG) test bus. Currently TMS and TCK are not connected, and TDI is shorted to TDO.

Pin description	
Terminal symbol	Description
A _n (n = 1 to 8)	Data inputs, A port
A _{On} (n = 1 to 8)	Data outputs, A port
B _n (n = 1 to 8)	Data inputs/outputs, B port
OEA, OEB, OEB	Output enable control inputs

FIGURE 1. Terminal connections.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 10

DESC FORM 193A
JUL 94

9004708 0027762 362

查询"5962-96815010XA"供应商

INPUTS			FUNCTION
OEB	$\overline{\text{OEB}}$	OEA	
L	X	L	Isolation
X	H	L	
L	X	H	$\overline{\text{Bn}}$ data to AOn bus
X	H	H	
H	L	L	$\overline{\text{AIn}}$ data to Bn bus
H	L	H	$\overline{\text{AIn}}$ data to Bn bus, $\overline{\text{Bn}}$ data to AOn bus

H = High voltage level
 L = Low voltage level
 X = Irrelevant

FIGURE 2. Truth table.

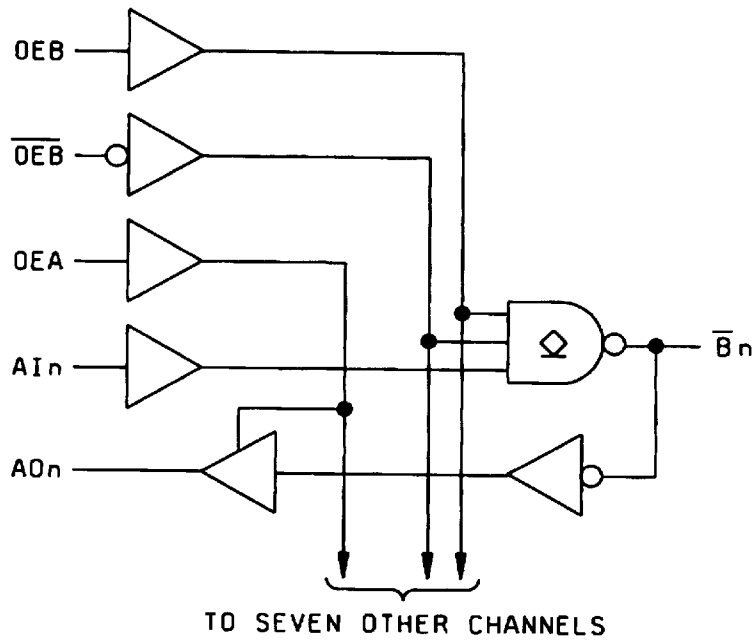


FIGURE 3. Logic diagram.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 11

DESC FORM 193A
 JUL 94

9004708 0027763 2T9

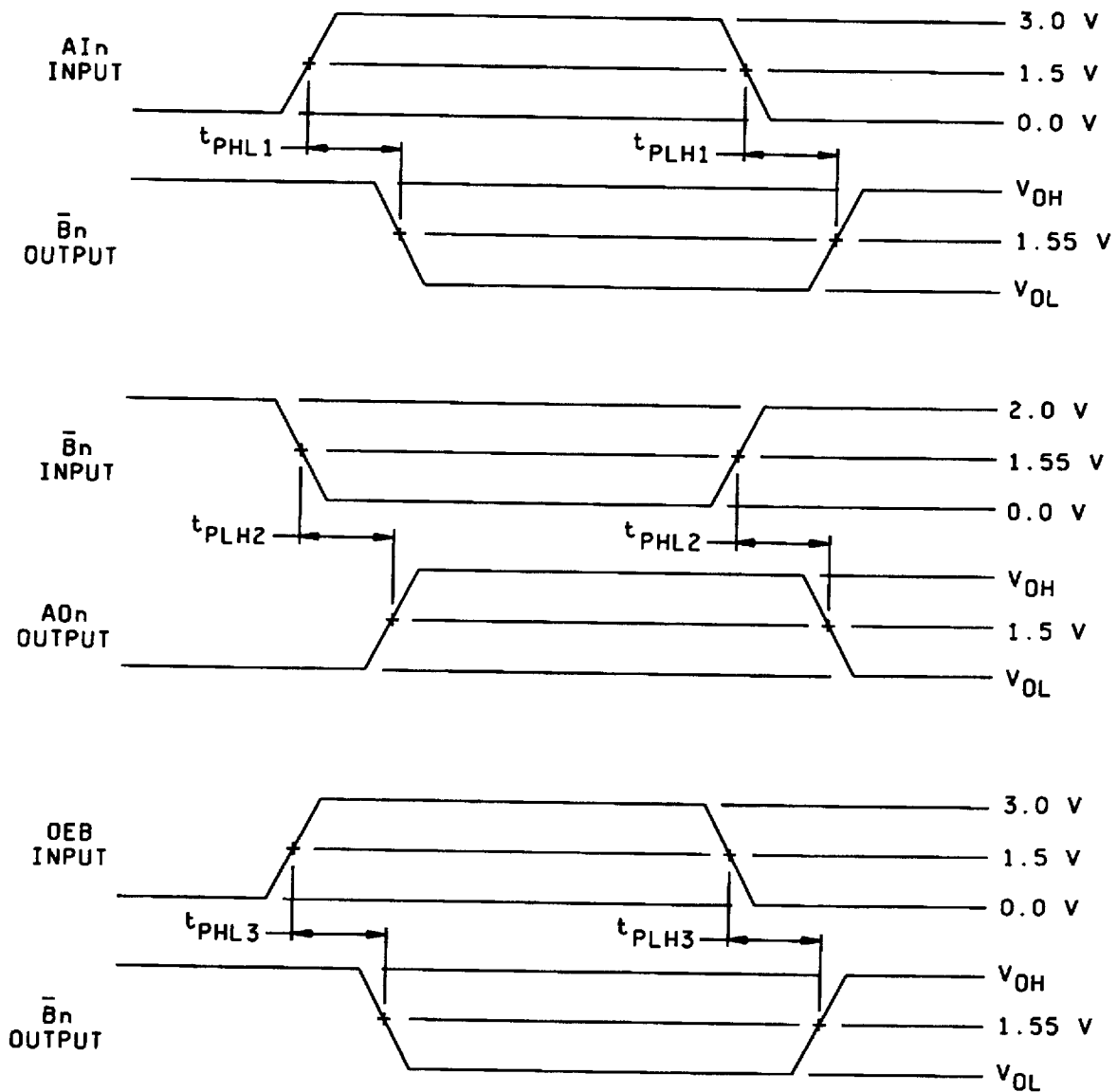


FIGURE 4. Switching waveforms and test circuit.

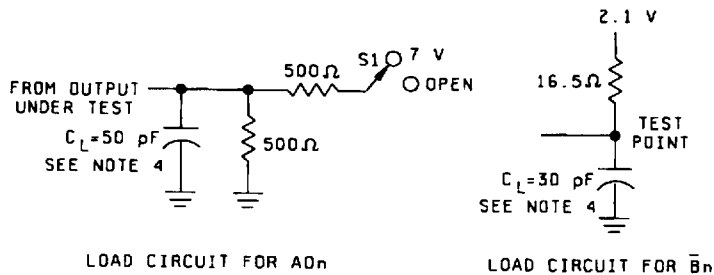
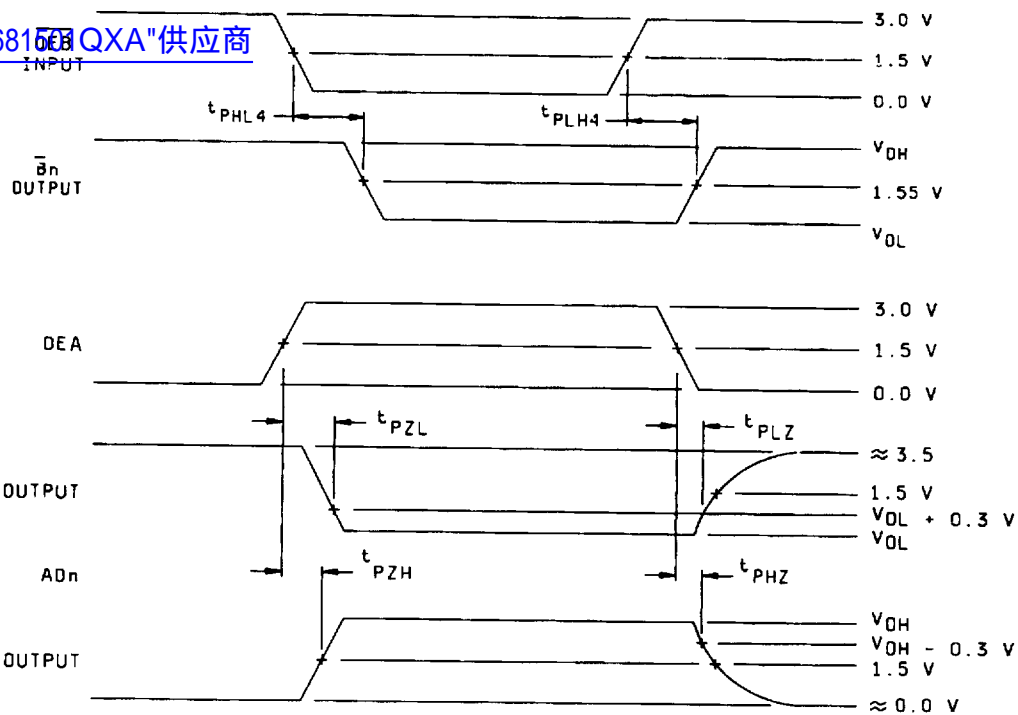
STANDARD
MICROCIRCUIT DRAWING
DEFENSE SUPPLY CENTER, COLUMBUS
COLUMBUS, OHIO 43216

SIZE
A

5962-96815

REVISION LEVEL

SHEET
12



NOTES:

1. When measuring t_{PLH} and t_{PHL} : S1 = open.
2. When measuring t_{PLZ} and t_{PZL} : S1 = 7 V
3. When measuring t_{PHZ} and t_{PZH} : S1 = open.
4. Capacitance, $C_L = 50$ pF minimum or equivalent (includes test jig and probe capacitance).
5. All input pulses are supplied by generators having the following characteristics: TTL inputs, $PRR \leq 10$ Mhz, $Z_O = 50\Omega$, $t_r \leq 2.5$ ns, $t_f \leq 2.5$ ns; BTL inputs, $PRR \leq 10$ Mhz, $Z_O = 50\Omega$, $t_r \leq 2.5$ ns, $t_f \leq 2.5$ ns.
6. $R_T = 50\Omega$ or equivalent.
7. Input signal from pulse generator: $V_{IN} = 0.0$ V to 3.0 V for A to B tests, and 1.0 V to 2.0 V for B to A tests; reference points are 1.5 V for A and output controls, and 1.55 V for B; $PRR \leq 10$ MHz; $t_r \leq 2.5$ ns; $t_f \leq 2.5$ ns; duty cycle = 50 percent.
8. Timing parameters shall be tested at a minimum input frequency of 1 MHz.
9. The outputs are measured one at a time with one transition per measurement.

FIGURE 4. Switching waveforms and test circuit - Continued.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 13

4.2.2 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QML in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table II herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.3.1 Electrostatic discharge sensitivity qualification inspection. Electrostatic discharge sensitivity (ESDS) testing shall be performed in accordance with MIL-STD-883, method 3015. ESDS testing shall be measured only for initial qualification and after process or design changes which may affect ESDS classification.

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-PRF-38535 permits alternate in-line control testing. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	---	---	1
Final electrical parameters (see 4.2)	1/ 1, 2, 3, 7, 8, 9, 10, 11	1/ 1, 2, 3, 7, 8, 9, 10, 11	2/ 1, 2, 3, 7, 8, 9, 10, 11
Group A test requirements (see 4.4)	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3, 7, 8, 9, 10, 11
Group D end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group E end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9	1, 7, 9

1/ PDA applies to subgroup 1.
2/ PDA applies to subgroups 1 and 7.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 14

4.4.1 Group A inspection.

a. Tests shall be as specified in table II herein.

[查询"5962-9681501QXA"供应商](#)

b. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table in figure 2 herein. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2, herein. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).

c. C_{IN} , C_{OUT} and $C_{I/O}$ shall be measured only for initial qualification and after process or design changes which may affect capacitance. C_{IN} , C_{OUT} and $C_{I/O}$ shall be measured between the designated terminal and GND at a frequency of 1 MHz. This test may be performed at 10 MHz and guaranteed, if not tested, at 1 MHz. The DC bias for the pin under test (V_{BIAS}) = 2.5 V or 3.0 V. For C_{IN} , C_{OUT} and $C_{I/O}$, test all applicable pins on five devices with zero failures.

For C_{IN} , C_{OUT} and $C_{I/O}$, a device manufacturer may qualify devices by functional groups. A specific functional group shall be composed of function types, that by design, will yield the same capacitance values when tested in accordance with table I, herein. The device manufacturer shall set a function group limit for the C_{IN} , C_{OUT} and $C_{I/O}$ tests. The device manufacturer may then test one device functional group, to the limits and conditions specified herein. All other device functions in that particular functional group shall be guaranteed, if not tested, to the limits and test conditions specified in table I, herein. The device manufacturers shall submit to DSCC-VA the device functions listed in each functional group and the test results for each device tested.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

- a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- b. $T_A = +125^\circ\text{C}$, minimum.
- c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table II herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at $T_A = +25^\circ\text{C} \pm 5^\circ\text{C}$, after exposure, to the subgroups specified in table II herein.
- c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

4.5 Methods of inspection. Methods of inspection shall be specified as follows:

4.5.1 Voltage and current. Unless otherwise specified, all voltages given are referenced to the microcircuit GND terminal. Currents given are conventional current and positive when flowing into the referenced terminal.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 15

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment design applications and logistics purposes).

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform Defense Supply Center, Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0525.

6.4 Comments. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43216-5000, or telephone (614) 692-0674.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER, COLUMBUS COLUMBUS, OHIO 43216	SIZE A		5962-96815
		REVISION LEVEL	SHEET 16

DESC FORM 193A
JUL 94

9004708 0027768 880

DATE: 96-06-12

Approved sources of supply for SMD 5962-96815 are listed below for immediate acquisition only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN <u>1/</u>	Vendor CAGE number	Vendor similar PIN <u>2/</u>
5962-9681501QXA	01295	SNJ54FB2040WD

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. The device manufacturers listed herein are authorized to supply alternate lead finishes "A", "B", or "C" at their discretion. Contact the listed approved source of supply for further information.

2/ **Caution.** Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number

01295

Vendor name and address

Texas Instruments Incorporated
 13500 N. Central Expressway
 P. O. Box 655303
 Dallas, TX 75265
 Point of contact: I-20 at FM 1788
 Midland, TX 79711-0448

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.

■ 9004708 0027769 717 ■